## 2SB740

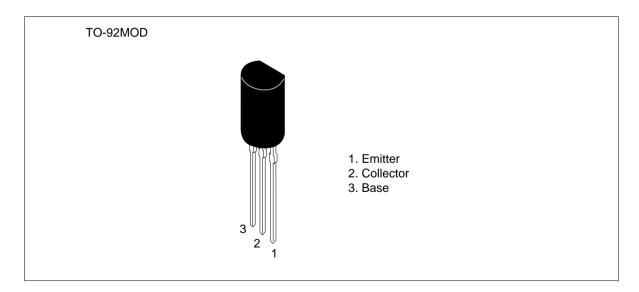
## Silicon PNP Epitaxial

# **HITACHI**

### **Application**

- Low frequency power amplifier
- Complementary pair with 2SD789

#### Outline





## 2SB740

### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

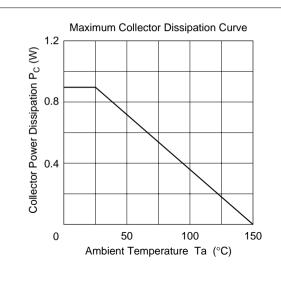
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	<b>-7</b> 0	V
Collector to emitter voltage	V <sub>CEO</sub>	-50	V
Emitter to base voltage	$V_{EBO}$	-6	V
Collector current	I <sub>c</sub>	<b>–1</b>	A
Collector power dissipation	P <sub>c</sub>	0.9	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

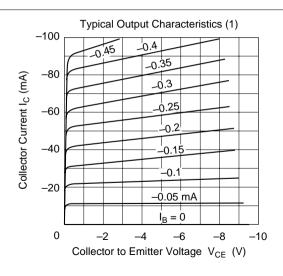
### **Electrical Characteristics** (Ta = 25°C)

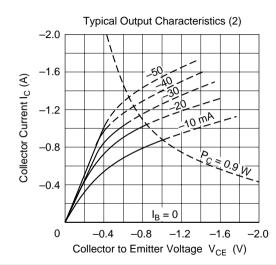
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\text{(BR)CBO}}$	-70	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	_	_	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	_	_	V	$I_{E} = -10 \mu\text{A}, \ I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	-1	μΑ	$V_{CB} = -55 \text{ V}, I_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_	_	-0.2	μΑ	$V_{EB} = -6 \text{ V}, I_{C} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	100	_	320		$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.6	V	$I_{c} = -1 \text{ A}, I_{B} = -0.1 \text{ A}$
Gain bandwidth product	f⊤	_	150	_	MHz	$V_{CE} = -2 \text{ V}, I_{C} = -10 \text{ mA}$
Collector output capacitance	Cob	_	35	_	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz

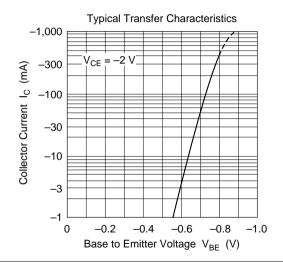
Note: 1. The 2SB740 is grouped by  $h_{FE}$  as follows.

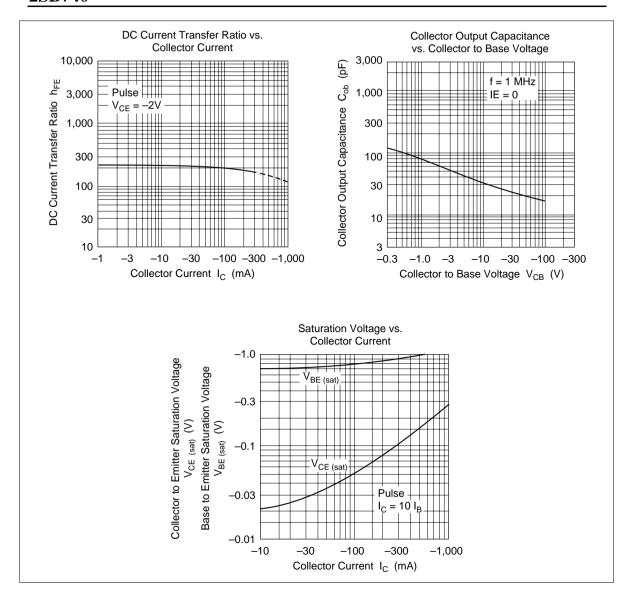
В	С
100 to 200	160 to 320



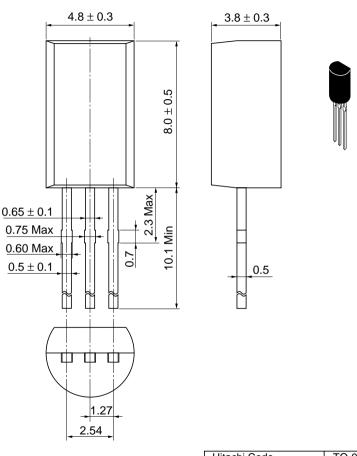








Unit: mm



Hitachi Code TO-92 Mod

JEDEC —

EIAJ Conforms

Weight (reference value) 0.35 g

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